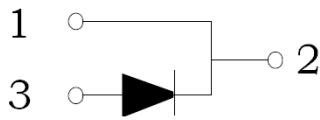


TO-220FAC

Ultrafast Recovery Diode in a TO-220FAC Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode



PIN1 2 Cathode

PIN 3 Anode

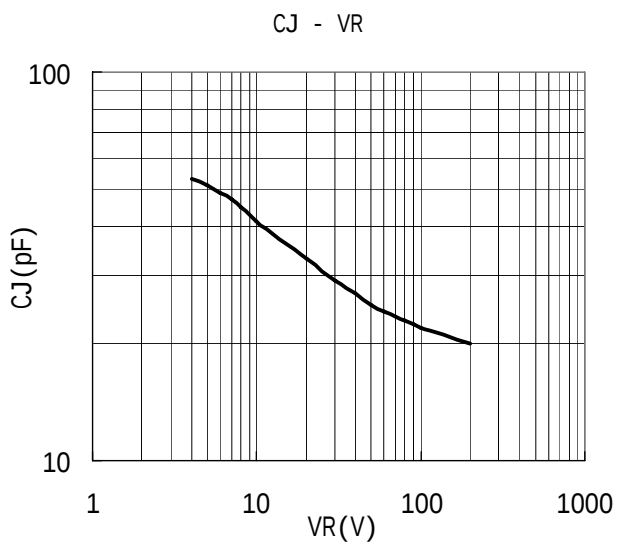
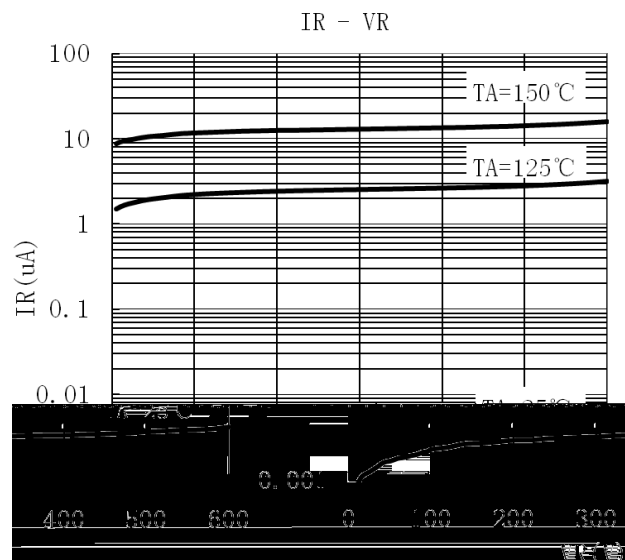
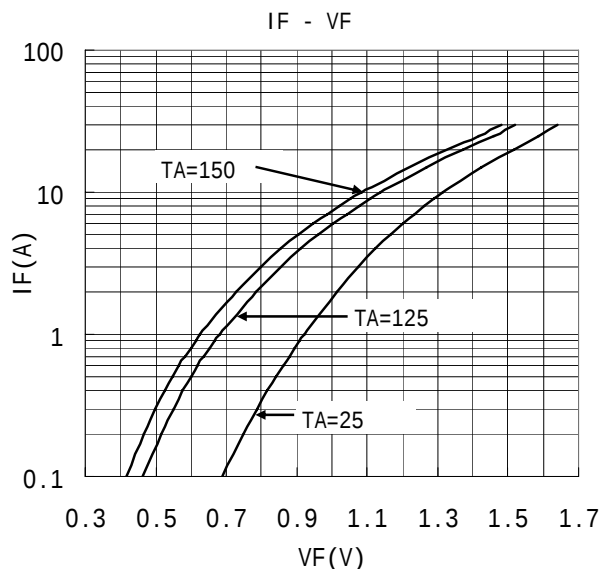
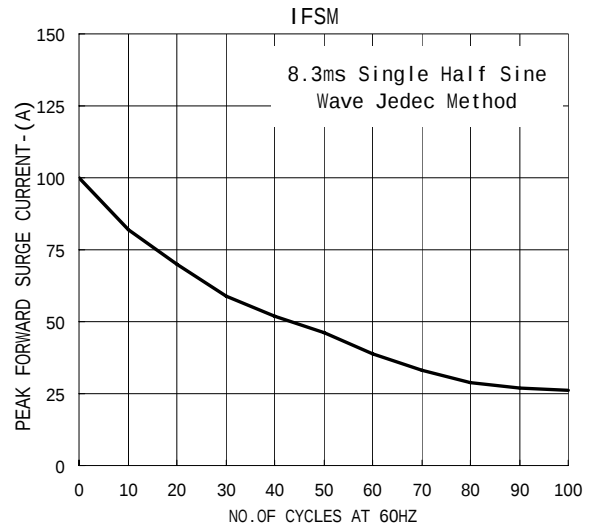
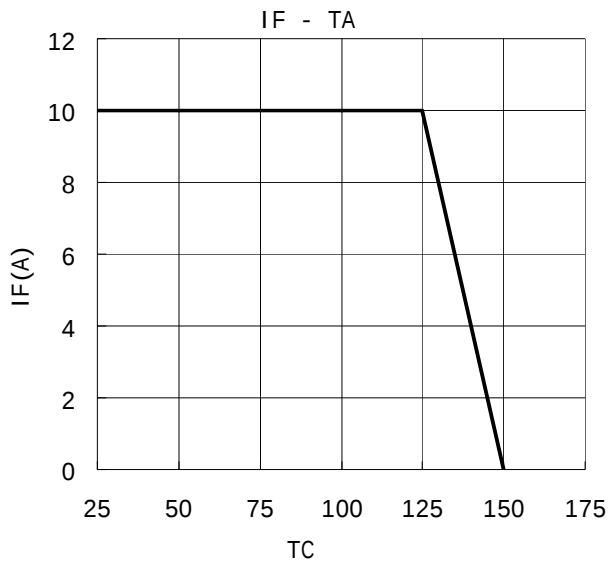
See Marking Instructions

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Forward Current	I_F	1×10	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	4	/W
Junction Temperature Range	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=1mA$	600			V
Forward Voltage	V_F	$I_F=2.0A \quad T_C=25$		1.0	1.2	V
		$I_F=2.0A \quad T_C=125$		0.80	1.0	
		$I_F=10A \quad T_C=25$		1.3	1.5	
		$I_F=10A \quad T_C=125$		1.2	1.4	
Instantaneous Reverse Current	I_R Note 1	$V_R=600V \quad T_a=25$			10	μA
		$V_R=600V \quad T_a=125$			500	
Reverse Recovery Time	t_{rr}	$I_F=0.5A \quad I_R=1.0A$ $I_{RR}=0.25A$			50	ns

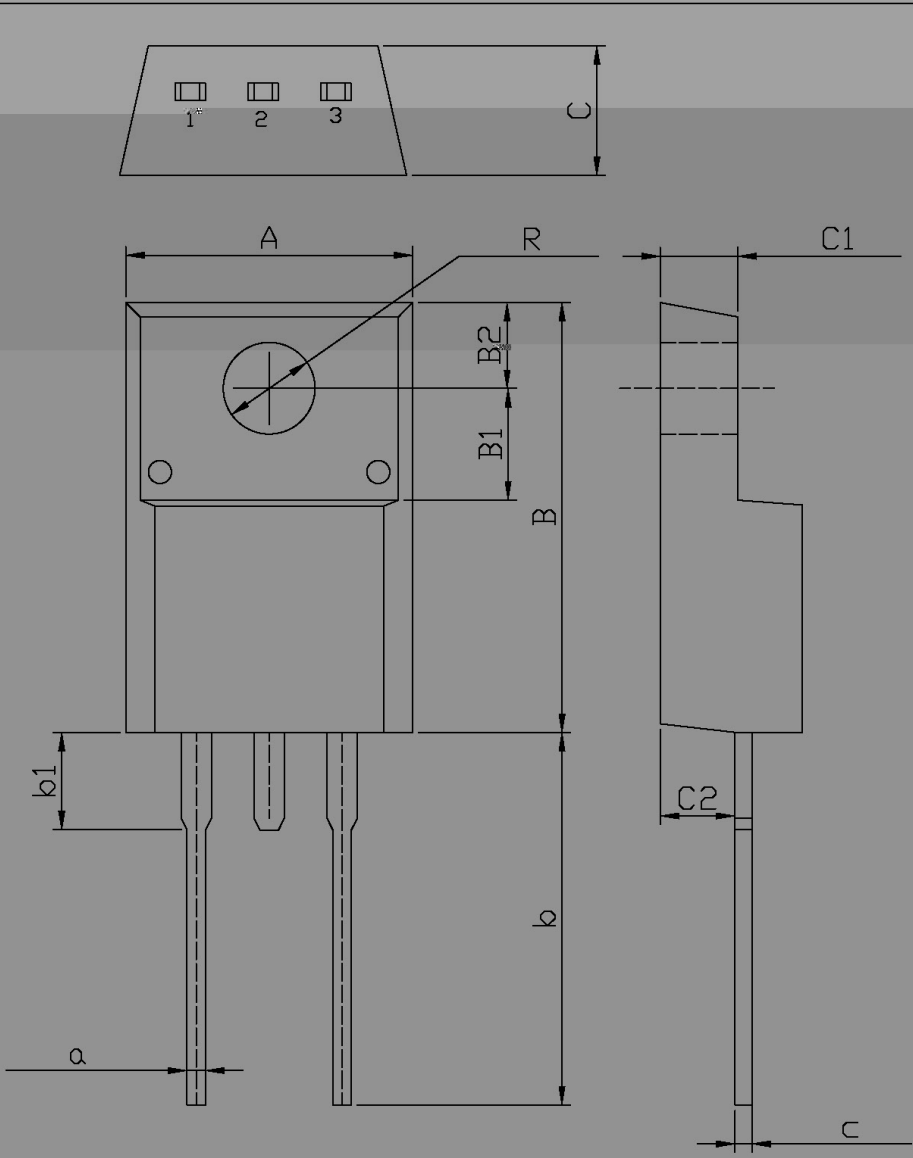
/Notes

1.

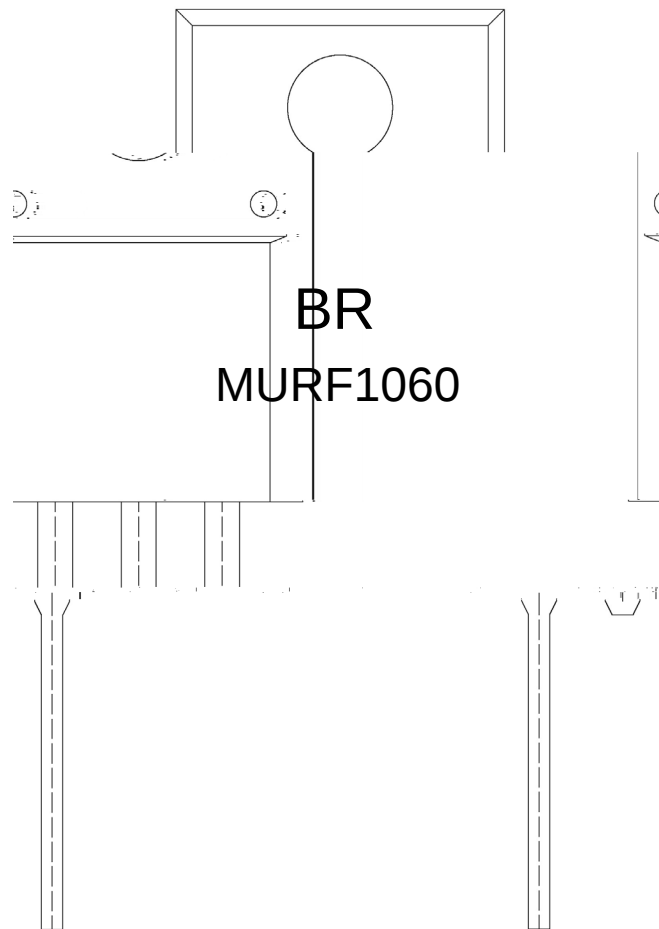


TO-220FAC

单位: mm



Symbol	Dimensions In. Millimeters		Symbol	Dimensions In. Millimeters	
	Min	Max		Min	Max
C	4.3	4.7	b1	2.8	2.8
A	9.7	10.3	a	6.35	6.75
B	14.7	15.3	b	11.18	11.58



BR

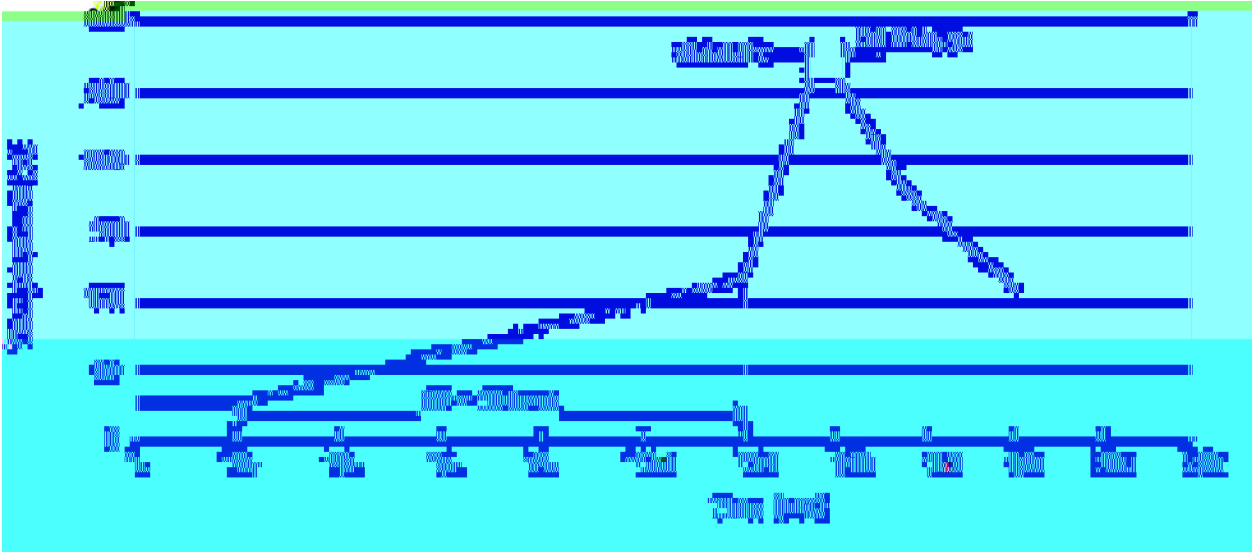
MURF1060

Note:

BR: Company Code

MURF1060 Product Type.

**** Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

255±5

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱